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SLPS259 - DECEMBER 2011

N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16415Q5

FEATURES

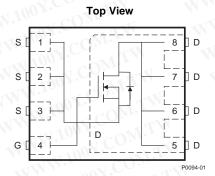
- **Ultralow Qg and Qgd**
- **Very Low On-Resistance**
- **Low Thermal Resistance**
- Avalanche Rated
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**

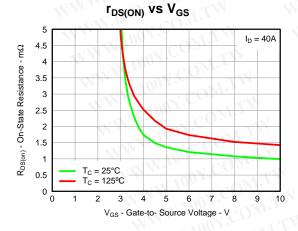
APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and **Computing Systems**
- **Optimized for Synchronous FET Applications**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





PRODUCT SUMMARY

V _{DS}	Drain-to-source voltage	25		V
Q_g	Gate charge, total (4.5 V)	21		nC
Q _{gd}	Gate charge, gate-to-drain	5.2		nC
	Drain to source on registeres	$V_{GS} = 4.5 \text{ V}$	1.5	mΩ
r _{DS(on)}	Drain-to-source on-resistance	V _{GS} = 10 V	0.99	mΩ
V _{GS(th)}	Threshold voltage	1.5	•	V

ORDERING INFORMATION

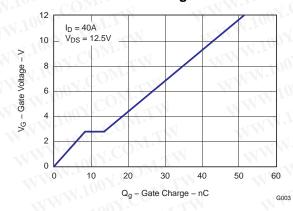
Device	Package	Media	Qty	Ship
CSD16415Q5	SON 5-mm × 6-mm plastic package	13-inch (33-cm) reel	2500	Tape and reel

ABSOLUTE MAXIMUM RATINGS

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain-to-source voltage	25	V
V_{GS}	Gate-to-source voltage	+16/-12	V
- T	Continuous drain current, T _C = 25°C	100	Α
ID	Continuous drain current ⁽¹⁾	38	Α
I _{DM}	Pulsed drain current, T _A = 25°C ⁽²⁾	200	Α
P_D	Power dissipation ⁽¹⁾	3.2	W
T _J , T _{STG}	Operating junction and storage temperature range	-55 to 150	°C
E _{AS}	Avalanche energy, single-pulse $I_D = 100 \text{ A}, L = 0.1 \text{ mH}, R_G = 25 \Omega$	500	mJ

- $R_{\theta JA} = 40^{\circ} \text{C/W on } 1 \text{in}^2 (6.45 \text{cm}^2) \text{ Cu } [2 \text{ oz. } (0.071 \text{mm})]$ thick)] on 0.060-inch (1.52-mm) thick FR4 PCB.
- Pulse duration ≤300 µs, duty cycle ≤2%

Gate Charge



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
naracteristics	ON:14	V. I. A.	,	
Drain-to-source voltage	V _{GS} = 0 V, I _D = 250 μA	25		V
Drain-to-source leakage current	V _{GS} = 0 V, V _{DS} = 20 V	WT	1	μΑ
Gate-to-source leakage current	$V_{DS} = 0 \text{ V}, V_{GS} = -12 \text{ V to } 16 \text{ V}$	OM.	100	nA
Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.2 1.5	1.9	V
Drain to source on registernes	$V_{GS} = 4.5 \text{ V}, I_D = 40 \text{ A}$	1.5	1.8	$m\Omega$
Drain-to-source on-resistance	$V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$	0.99	1.15	$m\Omega$
Transconductance	V _{DS} = 15 V, I _D = 40 A	168		S
Characteristics	001. W.I.M. M. 100	T. COM'I'	4	
Input capacitance	100 K.CO. TW WWW.	3150	4100	pF
Output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 12.5 \text{ V}, f = 1 \text{ MHz}$	2530	3300	pF
Reverse transfer capacitance	N.100 . COM: I. LANN'I	175	230	pF
Series gate resistance	1100X.C.M.TW	1.2	2.4	Ω
Gate charge total (4.5 V)	W. OOX.CO. THE WAY	21	29	nC
Gate charge, gate-to-drain	V 42.5 V ID 40.4	5.2	TV	nC
Gate charge, gate-to-source	V _{DS} = 12.5 V, ID = 40 A	8.3	1.1	nC
Gate charge at Vth	TIOOY.COMITW WY	4.8	M.I	nC
Output charge	V _{DS} = 15 V, V _{GS} = 0 V	55	117	nC
Turnon delay time	TAIN TO TO COMP.	16.6	O_{Lar}	ns
Rise time	$V_{DS} = 12.5 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 40 \text{ A}$	30	-OM	ns
Turnoff delay time	$R_G = 2 \Omega$	20		ns
Fall time	NAM. TON COM TAN	12.7	.Co.	ns
naracteristics	TNN TO ST COM.	MW.Io.	V.CO	Mr.
Diode forward voltage	I _S = 40 A, V _{GS} = 0 V	0.85	1	V
Reverse recovery charge	V _{DD} = 15 V, I _F = 40 A, di/dt = 300 A/μs	72	01.0	nC
Reverse recovery time	$V_{DD} = 15 \text{ V}, I_F = 40 \text{ A}, di/dt = 300 \text{ A/}\mu\text{s}$	45	onY.	ns
	Drain-to-source voltage Drain-to-source leakage current Gate-to-source leakage current Gate-to-source threshold voltage Drain-to-source on-resistance Transconductance Characteristics Input capacitance Output capacitance Reverse transfer capacitance Series gate resistance Gate charge total (4.5 V) Gate charge, gate-to-drain Gate charge at Vth Output charge Turnon delay time Rise time Turnoff delay time Fall time haracteristics Diode forward voltage Reverse recovery charge	paracteristics V _{GS} = 0 V, I _D = 250 μA Drain-to-source leakage current V _{GS} = 0 V, V _{DS} = 20 V Gate-to-source leakage current V _{DS} = 0 V, V _{DS} = -12 V to 16 V Gate-to-source threshold voltage V _{DS} = V _{GS} , I _D = 250 μA Drain-to-source on-resistance V _{DS} = V _{SS} , I _D = 250 μA V _{SS} = 4.5 V, I _D = 40 A V _{DS} = 10 V, I _D = 40 A V _{DS} = 10 V, I _D = 40 A V _{DS} = 15 V, I _D = 40 A Characteristics Input capacitance V _{DS} = 0 V, V _{DS} = 12.5 V, f = 1 MHz Reverse transfer capacitance V _{DS} = 0 V, V _{DS} = 12.5 V, ID = 40 A Series gate resistance V _{DS} = 12.5 V, ID = 40 A Gate charge total (4.5 V) V _{DS} = 15 V, V _{GS} = 0 V Gate charge, gate-to-source V _{DS} = 15 V, V _{GS} = 0 V Gate charge at Vth V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 40 A Output charge V _{DS} = 12.5 V, V _{GS} = 4.5 V, I _D = 40 A Rise time V _{DS} = 12.5 V, V _{GS} = 0 V Turnoff delay time R _G = 2 Ω Fall time V _{DD} = 15 V, I _F = 40 A, di/dt = 300 A/μs	Drain-to-source voltage V _{GS} = 0 V, I _D = 250 μA 25 Drain-to-source leakage current V _{GS} = 0 V, V _{DS} = 20 V Gate-to-source leakage current V _{DS} = 0 V, V _{GS} = −12 V to 16 V Gate-to-source threshold voltage V _{DS} = 0 V, V _{GS} = −12 V to 16 V Gate-to-source threshold voltage V _{DS} = V _{GS} , I _D = 250 μA 1.2 1.5 Drain-to-source on-resistance V _{GS} = 4.5 V, I _D = 40 A 0.99 Transconductance V _{DS} = 15 V, I _D = 40 A 168 Characteristics Input capacitance 3150 Output capacitance V _{SS} = 0 V, V _{DS} = 12.5 V, f = 1 MHz 2530 Reverse transfer capacitance 1.2 2530 Reverse transfer capacitance 1.2 2530 Series gate resistance 1.2 2530 Gate charge total (4.5 V) 21 21 Gate charge, gate-to-drain V _{DS} = 12.5 V, ID = 40 A 8.3 Gate charge, gate-to-source 0 8.3 Gate charge at Vth 0 4.8 Output charge V _{DS} = 15 V, V _{DS} = 0 V 55	Drain-to-source voltage V _{GS} = 0 V, I _D = 250 μA 25 Drain-to-source leakage current V _{GS} = 0 V, V _{DS} = 20 V 1 Gate-to-source leakage current V _{DS} = 0 V, V _{DS} = 20 V 100 Gate-to-source leakage current V _{DS} = 0 V, V _{DS} = -12 V to 16 V 100 Gate-to-source threshold voltage V _{DS} = V _{GS} , I _D = 250 μA 1.2 1.5 1.9 Drain-to-source on-resistance V _{GS} = 4.5 V, I _D = 40 A 0.99 1.15 1.8 Transconductance V _{DS} = 15 V, I _D = 40 A 0.99 1.15 Characteristics Input capacitance 3150 4100 Output capacitance 3150 4100 Coutput capacitance 7253 3300 Reverse transfer capacitance 1.2 2.4 Gate charge total (4.5 V) 21 29 Gate charge, gate-to-drain 5.2 3.3 Gate charge, gate-to-source 8.3 3.3 Gate charge at Vth 5.5 3.3 Output charge V _{DS} = 15 V, V _{GS} = 0 V 55 Turnor dela

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	MIN	TYP	MAX	UNIT
R _{0JC}	Thermal resistance, junction-to-case ⁽¹⁾	TANAN TA CO	DIVI	1.1	°C/W
R _{θJA}	Thermal resistance, junction-to-ambient (1) (2)	W. 100 F.	OMIT	50	°C/W

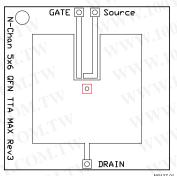
⁽¹⁾ R_{θJC} is determined with the device mounted on a 1-inch (2.54-cm) square, 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.060-inch (1.52-mm) thick FR4 board. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.

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⁽²⁾ Device mounted on FR4 material with 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



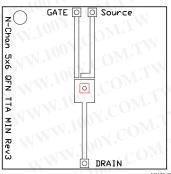
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Max $R_{\theta JA} = 50^{\circ}C/W$ when mounted on 1 inch2 (6.45 cm2) of 2-oz. (0.071-mm thick) Cu.

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Max $R_{\theta JA} = 121^{\circ}C/W$ when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

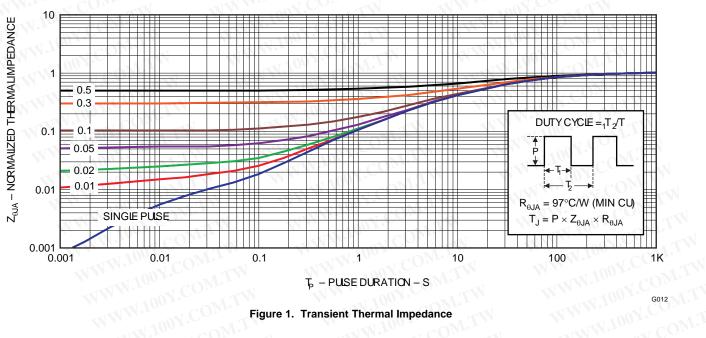


Figure 1. Transient Thermal Impedance

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

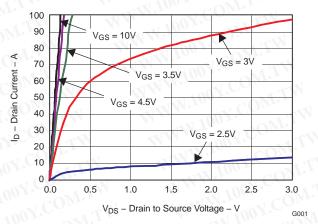
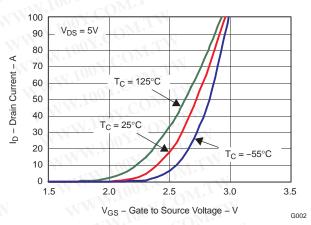


Figure 2. Saturation Characteristics



INSTRUMENTS

Figure 3. Transfer Characteristics

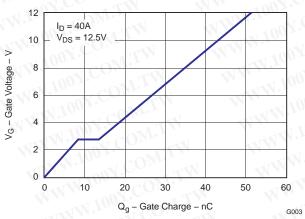


Figure 4. Gate Charge

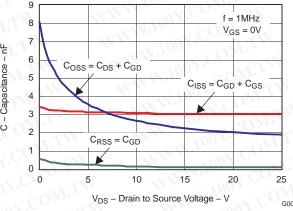


Figure 5. Capacitance

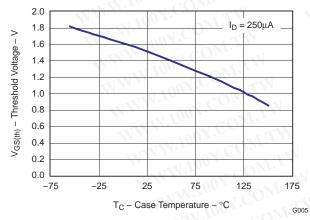


Figure 6. Threshold Voltage vs. Temperature

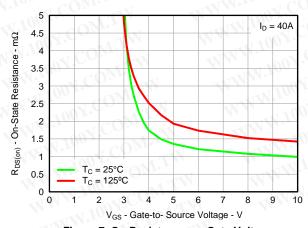


Figure 7. On-Resistance vs. Gate Voltage



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TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

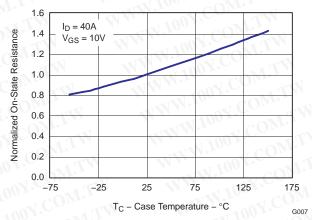


Figure 8. On-Resistance vs. Temperature

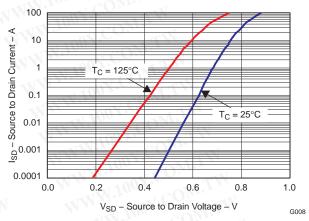


Figure 9. Typical Diode Forward Voltage

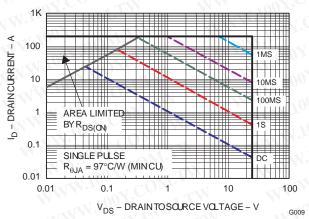


Figure 10. Maximum Safe Operating Area

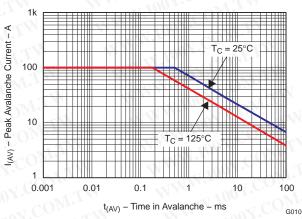


Figure 11. Single-Pulse Unclamped Inductive Switching

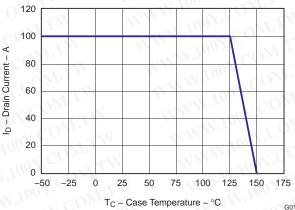
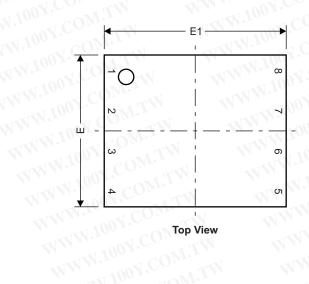


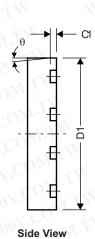
Figure 12. Maximum Drain Current vs. Temperature

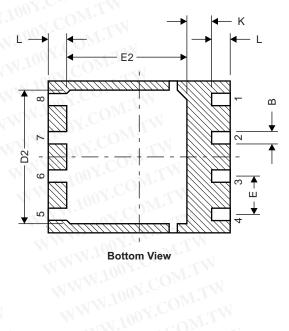


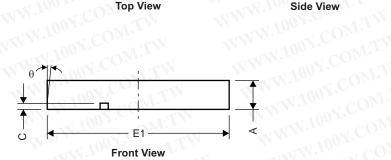
MECHANICAL DATA

Q5 Package Dimensions





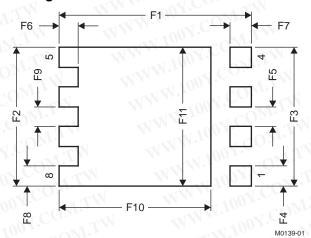




DIM ON!	MILLIM	ETERS	INC	CHES	COMIT
DIM	MIN V	MAX	MIN	MAX	T.COM.TN
V COM.	0.950	1.050	0.037	0.039	N.CO. TW
b	0.360	0.460	0.014	0.018	COM.
C	0.150	0.250	0.006	0.010	m. COWIL
c1 (1)	0.150	0.250	0.006	0.010	100Y.C. OM.TW
D1	4.900	5.100	0.193	0.201	. CON.CO. TY
D2	4.320	4.520	0.170	0.178	N. To. COM.
E 1007	4.900	5.100	0.193	0.201	7 100 r. COM:1
E1	5.900	6.100	0.232	0.240	1100Y.
E2	3.920	4.12	0.154	0.162	M. YOUX COM
e 100	1.27	TYP	100 ON 0.	.050	M. In COM
K	0.760	N.	0.030		17.100 r. COL
TEN NO.	0.510	0.710	0.020	0.028	MW 1001.
θ	0.00		M. r. COn		WWW. COV.CO

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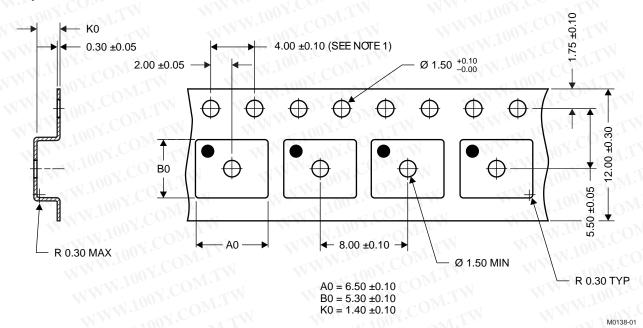
Figure 13. Recommended PCB Pattern



500Y.	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180
•	-11/			

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm IN 100 mm, noncumulative over 250 mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



PACKAGE OPTION ADDENDUM

24-Dec-2011

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
CSD16415Q5	ACTIVE	SON	DQH	8	2500	Pb-Free (RoHS	CU SN	Level-1-260C-UNLIM	
						Exempt)			

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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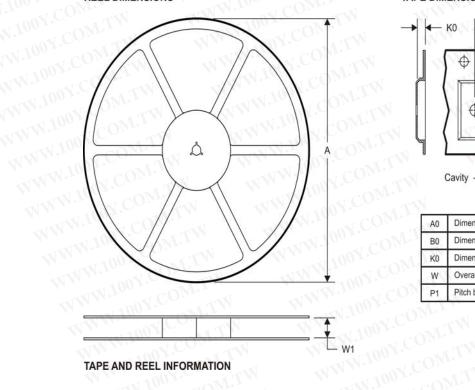
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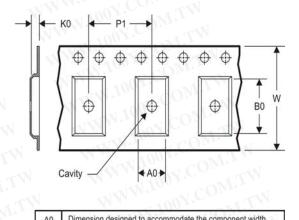
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TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



B0 Dimension designed to accommodate the component leng K0 Dimension designed to accommodate the component thick W Overall width of the carrier tape	
	ickness
W Overall width of the carrier tane	
VV Overdil modifier the conflor tape	
P1 Pitch between successive cavity centers	Mrs

100Y.COM.TW

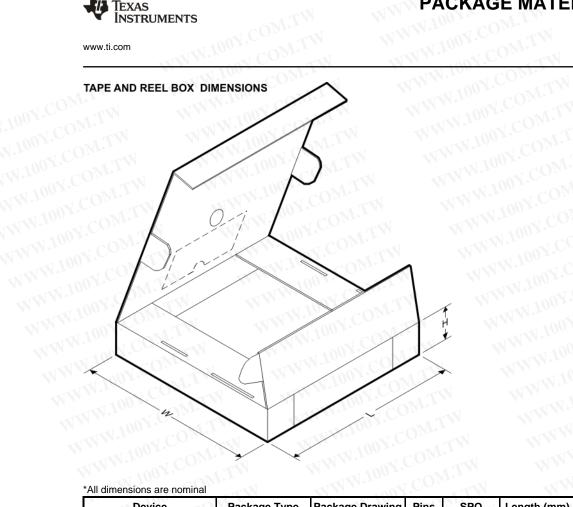
TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadran
CSD16415Q5	SON	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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*All dimensions are nominal

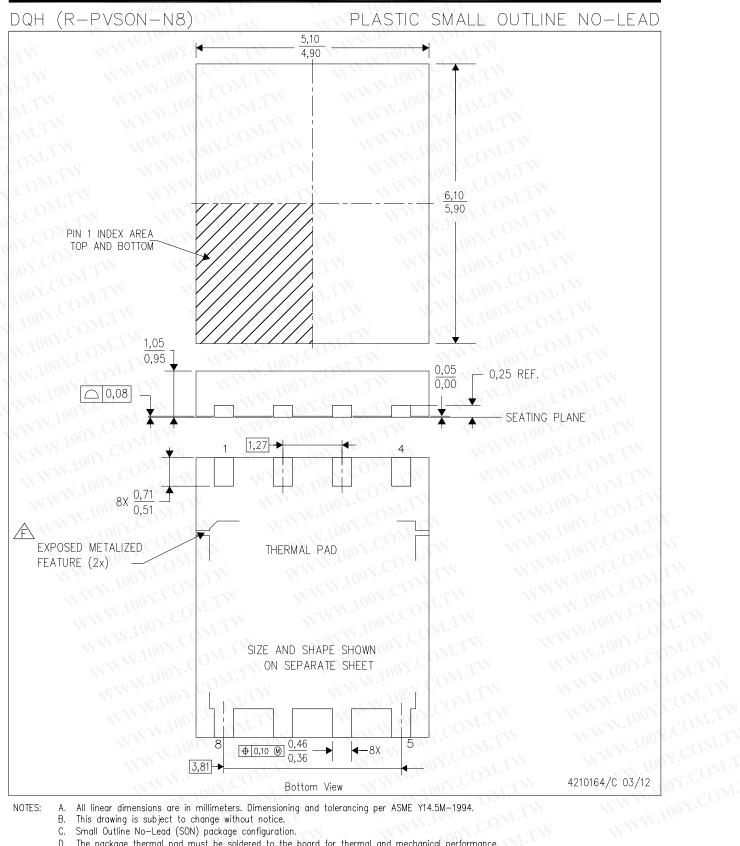
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD16415Q5	SON	DQH	8	2500	335.0	335.0	32.0

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- NOTES: All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - Small Outline No-Lead (SON) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
 - Metalized features are supplier options and may not be on the package.



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